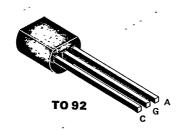TAG SEMICONDUCTORS LTD

X0103BA – X0103NA SCR'S

0.8 A   200–800 V   20–200 µA

The X0103 series silicon controlled rectifiers are high performance PNPN devices diffused with TAG's proprietary Top Glass™ Process. These parts are intended for general purpose, high speed, high voltage applications.

TO 92

Absolute Maximum Ratings $T_A = 25\,°C$ unless otherwise noted

Parameter	Part Nr.	Symbol	Min.	Max.	Unit	Test Conditions
Repetitive Peak Off State Voltage	X0103BA	V_{DRM} / V_{RRM}	200		V	$T_j = -40\,°C$ to $125\,°C$, $R_{GK} = 1\,K\Omega$
	X0103DA		400		V	
	X0103MA		600		V	
	X0103NA		800		V	
On-State Current		$I_{T(RMS)}$	0.8		A	All Conduction Angles $T_C = 55\,°C$
Average On-State Current		$I_{T(AV)}$	0.5		A	Half Cycle, $\Theta = 180°$, $T_C = 55\,°C$
Nonrept. On-State Current		I_{TSM}	9		A	Half Cycle, 60 Hz
Nonrept. On-State Current		I_{TSM}	8		A	Half Cycle, 50 Hz
Fusing Current		I^2t	0.32		A^2s	$t = 10$ ms, Half Cycle
Peak Reverse Gate Voltage		V_{GRM}	8		V	$I_{GR} = 10\,µA$
Peak Gate Current		I_{GM}	1		A	$10\,µs$ max.
Peak Gate Dissipation		P_{GM}	2		W	$10\,µs$ max.
Gate Dissipation		$P_{G(AV)}$	0.1		W	20 ms max.
Operating Temperature		T_j	−55	125	°C	
Storage Temperature		T_{stg}	−65	150	°C	
Soldering Temperature		T_{sld}		250	°C	1.6 mm from case, 10 s max.

X01

Electrical Characteristics $T_A = 25\,°C$ unless otherwise noted

Parameter	Symbol	Min.	Max.	Unit	Test Conditions
Off-State Leakage Current	I_{DRM}/I_{RRM}		0.1	mA	@$V_{DRM} + V_{RRM}$, $R_{GK} = 1\,K\Omega$, $T_j = 125\,°C$
Off-State Leakage Current	I_{DRM}/I_{RRM}		5	µA	@$V_{DRM} + V_{RRM}$, $R_{GK} = 1\,K\Omega$, $T_j = 25\,°C$
On-State Voltage	V_T		1.50	V	at $I_T = 1.6\,A$, $T_j = 25\,°C$
On-State Threshold Voltage	$V_{T(TO)}$		0.9	V	$T_j = 125\,°C$
On-State Slope Resistance	r_T		400	mΩ	$T_j = 125\,°C$
Gate Trigger Current	I_{GT}	20	200	µA	$V_D = 7\,V$
Gate Trigger Voltage	V_{GT}		0.8	V	$V_D = 7\,V$
Holding Current	I_H		5	mA	$R_{GK} = 1\,K\Omega$
Latching Current	I_L		6	mA	$R_{GK} = 1\,K\Omega$
Critical Rate of Voltage Rise	dv/dt	100		V/µs	$V_D = .67 \times V_{DRM}$ $R_{GK} = 1\,K\Omega$ $T_j = 125\,°C$
Critical Rate of Current Rise	di/dt	30		A/µs	$I_G = 10\,mA$ $di_G/dt = 0.1\,A/µs$ $T_j = 125\,°C$
Gate Controlled Delay Time	t_{gd}		1.0	µs	$I_G = 10\,mA$ $di_G/dt = 0.1\,A/µs$
Commutated Turn-Off Time	t_q		100	µs	$T_C = 85\,°C$ $V_D = .67 \times V_{DRM}$ $V_R = 35\,V$ $I_T = I_{T(AV)}$
Thermal Resistance junc. to case	$R_{\Theta jc}$		100	K/W	
Thermal Resistance junc. to amb.	$R_{\Theta ja}$		200	K/W	